

AMENDMENTS TO THE SPECIFICATION:

Please amend paragraph [0035] as follows:

The second portion 126 of SiGe layer 104, as shown in Figure 7, is removed revealing a first void 130, as shown in Figure 8, between the semiconductor layer 102 and the second portion 124 of silicon layer 106. Examples of suitable ways to remove second portion 126 of SiGe layer 104 include, but are not limited to, wet etching, RIE, or any combinations thereof. The first void 130 has the volume under the second portion 124 of silicon layer 106. However, additional material 132 of SiGe layer 104 may also be removed during this step. The removal is done selective to the material of semiconductor substrate 102. Some of the second portion 126 of SiGe layer 104 may have already been removed during the step of removing first portion 116 of SiGe layer 104. The remaining SiGe layer 104, silicon layer 106, first blocking layer 110, and polysilicon layer 112 act to support second portion 124 of silicon layer 106 over first void 130.